

# AP3401B 30V P-Channel Enhancement Mode MOSFET

## • General Description

AP3401B combines advanced MOSFET technology with a low resistance package to provide extremely low  $R_{DS(ON)}$ . This device is most suitable to load-switch or PWM applications.

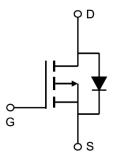
## Applications

- DC/DC converter for portable devices
- Load switch

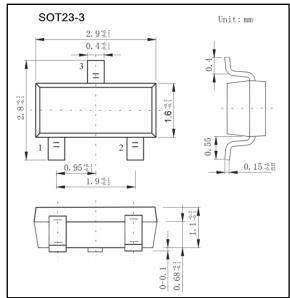
## Product Summary

 $R_{DS(ON)}$  (at  $V_{GS} = -2.5V$ )

$V_{ extsf{DS}}$	-30V
$I_D$ (at $V_{GS} = -10V$ )	-4.2A
$R_{DS(ON)}$ (at $V_{GS} = -10V$ )	$< 50 \mathrm{m}\Omega$
$R_{DS(ON)}$ (at $V_{GS} = -4.5V$ )	< 65mΩ











## • Absolute Maximum Ratings Ta = 25°C

Parameter		Symbol	Rating	Unit	
Drain-Source Voltage		$V_{DS}$	-30	V	
Gate-Source Voltage		$V_{GS}$	±12	V	
Continuous Drain Current	T <sub>A</sub> =25°C	I I I	-4.2		
	$T_A = 70^{\circ}C$		-3.5	Α	
Pulsed Drain Current *		I <sub>DM</sub>	-30	1	
Power Dissipation	pation T <sub>A</sub> = 25°C	1.4	\A/		
	$T_A = 70^{\circ}C$	$P_{D}$	1	W	
Thermal Resistance. Junction-to-Ambient	t ≤ 10s	D	90		
Thermal Resistance. Junction-to-Ambient		$R_{ hetaJA}$	125	°C/W	
Thermal Resistance. Junction-to-Case		$R_{\theta JC}$	60		
Junction Temperature		Tı	150	°C	
Junction and Storage Temperature Range		Тѕтс	-55 to 150	]	

<sup>\*</sup> Repetitive rating, pulse width limited by junction temperature.

 $< 120 m\Omega$ 

## **AP3401B**

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#### • Electrical Characteristics Ta = 25°C

Parameter	Symbol	Test Conditions	Min	Тур	Max	Unit	
Drain-Source Breakdown Voltage	$V_{DSS}$	$I_D = -250 \mu A$ , $V_{GS} = 0 V$	-30			V	
Zero Gate Voltage Drain Current	I <sub>DSS</sub>	V <sub>DS</sub> =-24V, V <sub>GS</sub> =0V			-1	1	
		$V_{DS}$ =-24V, $V_{GS}$ =0V, $T_{J}$ =55°C			-5	μΑ	
Gate-Body leakage current	$I_{GSS}$	V <sub>DS</sub> =0V, V <sub>GS</sub> =±12V			±100	nA	
Gate Threshold Voltage	$V_{GS(th)}$	$V_{DS}=V_{GS}$ , $I_{D}=-250\mu A$	-0.4	-1	-1.3	V	
Static Drain-Source On-Resistance	R <sub>DS(ON)</sub>	V <sub>GS</sub> =-10V, I <sub>D</sub> =-4.2A		42	50	mΩ	
		$V_{GS}$ =-10V, $I_{D}$ =-4.2A $T_{J}$ =125°C			75		
		$V_{GS}$ =-4.5V, $I_{D}$ =-4A		53	65		
		$V_{GS}$ =-2.5V, $I_{D}$ =-1A		80	120		
On state drain current	$I_{D(ON)}$	V <sub>GS</sub> =-4.5V, V <sub>DS</sub> =-5V	-25			A	
Forward Transconductance	$\mathbf{g}_{FS}$	$V_{DS}$ =-5V, $I_D$ =-5A	7	11		S	
Input Capacitance	$C_{iss}$	V <sub>GS</sub> =0V, V <sub>DS</sub> =-15V, f=1MHz		954		pF	
Output Capacitance	$C_{oss}$			115			
Reverse Transfer Capacitance	$C_{rss}$			77			
Gate Resistance	Rg	V <sub>GS</sub> =0V, V <sub>DS</sub> =0V, f=1MHz		6		Ω	
Total Gate Charge	$Q_{\mathrm{g}}$			9.4		nC	
Gate Source Charge	$Q_{\mathrm{gs}}$	$V_{GS}$ =-4.5V, $V_{DS}$ =-15V, $I_{D}$ =-4A		2			
Gate Drain Charge	$Q_{\mathrm{gd}}$			3			
Turn-On Delay Time	$t_{D(on)}$			6.3		ns	
Turn-On Rise Time	$t_r$	$V_{GS}\text{=-}10\text{V, }V_{DS}\text{=-}15\text{V,}$ $R_{L}\text{=}3.6\Omega, R_{GEN}\text{=}6\Omega$		3.2			
Turn-Off Delay Time	$t_{\mathrm{D(off)}}$			38.3			
Turn-Off Fall Time	$t_{\mathrm{f}}$			12			
Body Diode Reverse Recovery Time	$t_{\mathrm{rr}}$	$I_F$ =-4A, $d_I/d_t$ =100A/ $\mu$ s 20		20.2			
Body Diode Reverse Recovery Charge	$Q_{rr}$	$I_F$ =-4A, $d_I/d_t$ =100A/ $\mu$ s		11.2		nC	
Maximum Body-Diode Continuous Current	$I_S$				-2.2	A	
Diode Forward Voltage	$V_{SD}$	$I_S=-1A$ , $V_{GS}=0V$		-0.75	-1	V	

### • Ordering Information

Ordering Part Number	Package	MOQ
AP3401B	SOT23-3	3,000 pcs / reel

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#### • Typical Characteristics

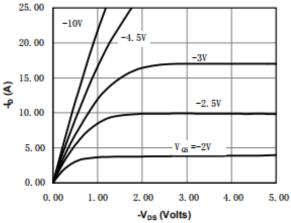


Fig 1: On-Region Characteristics

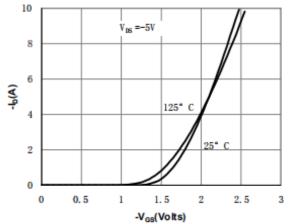


Figure 2: Transfer Characteristics

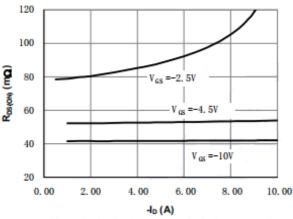


Figure 3: On-Resistance vs. Drain Current and Gate Voltage

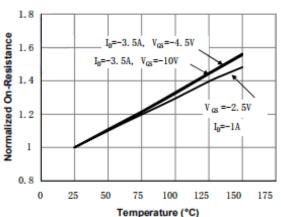


Figure 4: On-Resistance vs. Junction Temperature

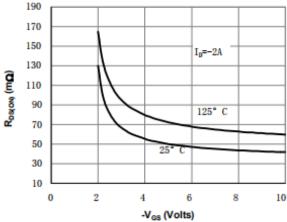


Figure 5: On-Resistance vs. Gate-Source Voltage

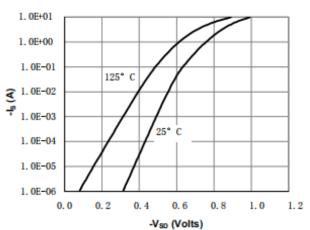


Figure 6: Body-Diode Characteristics



#### • Typical Characteristics

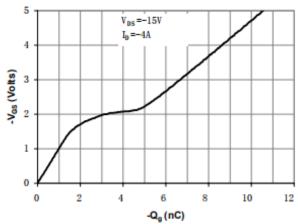


Figure 7: Gate-Charge Characteristics

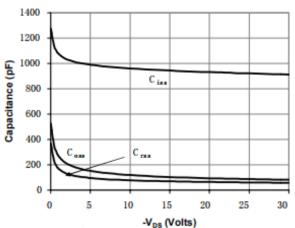


Figure 8: Capacitance Characteristics

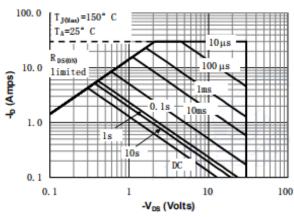


Figure 9: Maximum Forward Biased Safe Operating Area (Note E)

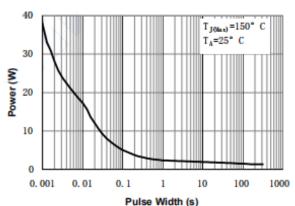


Figure 10: Single Pulse Power Rating Junction-to-Ambient (Note E)

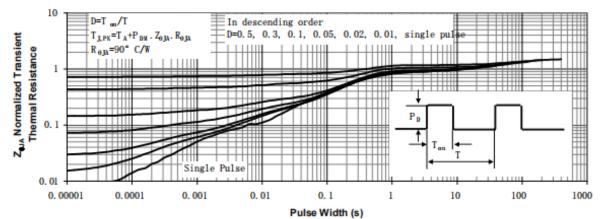


Figure 11: Normalized Maximum Transient Thermal Impedance

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